

# DS91D176/DS91C176 100 MHz Single Channel M-LVDS Transceivers

Check for Samples: DS91C176, DS91D176

#### **FEATURES**

- DC to 100+ MHz / 200+ Mbps Low Power, Low EMI Operation
- Optimal for ATCA, uTCA Clock Distribution Networks
- Meets or Exceeds TIA/EIA-899 M-LVDS Standard
- Wide Input Common Mode Voltage for Increased Noise Immunity
- DS91D176 has Type 1 Receiver Input
- DS91C176 has Type 2 Receiver with Fail-safe
- Industrial Temperature Range
- Space Saving SOIC-8 Package

#### **DESCRIPTION**

The DS91C176 and DS91D176 are 100 MHz single channel M-LVDS (Multipoint Low Voltage Differential Signaling) transceivers designed for applications that utilize multipoint networks (e.g. clock distribution in ATCA and uTCA based systems). M-LVDS is a new bus interface standard (TIA/EIA-899) optimized for multidrop networks. Controlled edge rates, tight input receiver thresholds and increased drive strength are sone of the key enhancements that make M-LVDS devices an ideal choice for distributing signals via multipoint networks.

The DS91C176/DS91D176 are half-duplex transceivers that accept LVTTL/LVCMOS signals at the driver inputs and convert them to differential M-LVDS signals. The receiver inputs accept low voltage differential signals (LVDS, B-LVDS, M-LVDS, LV-PECL and CML) and convert them to 3V LVCMOS signals. The DS91D176 has a M-LVDS type 1 receiver input with no offset. The DS91C176 has an M-LVDS type 2 receiver which enable failsafe functionality.

# Typical Application in an ATCA Clock Distribution Network

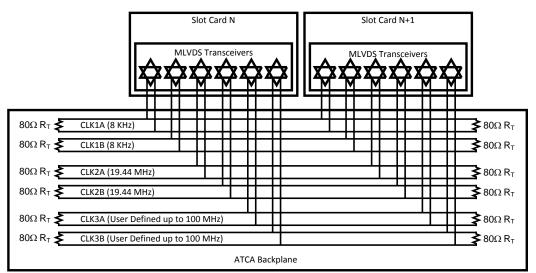


Figure 1. System Diagram

ΔΔ

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



## **Connection and Logic Diagram**

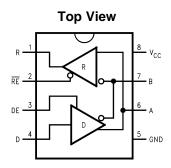


Figure 2. SOIC Package See Package Number D0008A

## **M-LVDS** Receiver Types

The EIA/TIA-899 M-LVDS standard specifies two different types of receiver input stages. A type 1 receiver has a conventional threshold that is centered at the midpoint of the input amplitude,  $V_{ID}/2$ . A type 2 receiver has a built in offset that is 100mV greater than  $V_{ID}/2$ . The type 2 receiver offset acts as a failsafe circuit where open or short circuits at the input will always result in the output stage being driven to a low logic state.

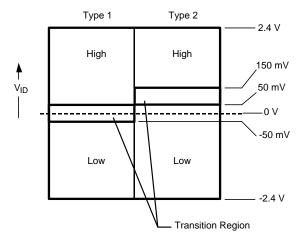


Figure 3. M-LVDS Receiver Input Thresholds



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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# Absolute Maximum Ratings (1)(2)

Supply Voltage, V <sub>CC</sub>	-0.3V to +4V
Control Input Voltages	$-0.3V$ to $(V_{CC} + 0.3V)$
Driver Input Voltage	$-0.3V$ to $(V_{CC} + 0.3V)$
Driver Output Voltages	-1.8V to +4.1V
Receiver Input Voltages	-1.8V to +4.1V
Receiver Output Voltage	$-0.3V$ to $(V_{CC} + 0.3V)$
Maximum Package Power Dissipation at +25°C	
SOIC Package	833 mW
Derate SOIC Package	6.67 mW/°C above +25°C
Thermal Resistance (4-Layer, 2 oz. Cu, JEDEC)	
$\theta_{JA}$	150°C/W
$\theta_{ m JC}$	63°C/W
Maximum Junction Temperature	150°C
Storage Temperature Range	−65°C to +150°C
Lead Temperature (Soldering, 4 seconds)	260°C
ESD Ratings: (HBM 1.5kΩ, 100pF)	≥ 8 kV
(EIAJ 0Ω, 200pF)	≥ 250 V
(CDM 0Ω, 0pF)	≥ 1000 V

<sup>(1) &</sup>quot;Absolute Maximum Ratings" are those beyond which the safety of the device cannot be verified. They are not meant to imply that the device should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

# **Recommended Operating Conditions**

	Min	Тур	Max	Units
Supply Voltage, V <sub>CC</sub>	3.0	3.3	3.6	V
Voltage at Any Bus Terminal (Separate or Common-Mode)	-1.4		+3.8	V
Differential Input Voltage V <sub>ID</sub>			2.4	V
LVTTL Input Voltage High V <sub>IH</sub>	2.0		V <sub>CC</sub>	V
LVTTL Input Voltage Low V <sub>IL</sub>	0		0.8	V
Operating Free Air Temperature T <sub>A</sub>	-40	+25	+85	°C

### **Electrical Characteristics**

Over recommended operating supply and temperature ranges unless otherwise specified. (1) (2) (3) (4)

	Parameter	Test Conditions	Min	Тур	Max	Units
M-LVDS D	river					
V <sub>AB</sub>	Differential output voltage magnitude	$R_L = 50\Omega$ , $C_L = 5pF$	480		650	mV
$\Delta V_{AB}$	Change in differential output voltage magnitude between logic states	See Figure 4 and Figure 6	-50	0	+50	mV
V <sub>OS(SS)</sub>	Steady-state common-mode output voltage	$R_L = 50\Omega$ , $C_L = 5pF$	0.3	1.8	2.1	V
$ \Delta V_{OS(SS)} $	Change in steady-state common-mode output voltage between logic states	See Figure 4 and Figure 5 (V <sub>OS(PP)</sub> @ 500KHz clock)	0		+50	mV
V <sub>OS(PP)</sub>	Peak-to-peak common-mode output voltage			135		mV
V <sub>A(OC)</sub>	Maximum steady-state open-circuit output voltage	See Figure 7	0		2.4	V
V <sub>B(OC)</sub>	Maximum steady-state open-circuit output voltage		0		2.4	V

<sup>(1)</sup> All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to device ground unless otherwise specified.

<sup>(2)</sup> If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.

<sup>(2)</sup> All typicals are given for  $V_{CC} = 3.3V$  and  $T_A = 25$ °C.

<sup>(3)</sup> The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this datasheet.

<sup>(4)</sup> C<sub>L</sub> includes fixture capacitance and C<sub>D</sub> includes probe capacitance.



## **Electrical Characteristics (continued)**

Over recommended operating supply and temperature ranges unless otherwise specified. (1) (2) (3) (4)

	Parameter	Test Conditions	5	Min	Тур	Max	Units
$V_{P(H)}$	Voltage overshoot, low-to-high level output	$R_L = 50\Omega, C_L = 5pF, C_D = 0$	.5pF			1.2V <sub>SS</sub>	V
$V_{P(L)}$	Voltage overshoot, high-to-low level output	See Figure 9 and Figure 10 <sup>(5)</sup>		-0.2V ss			V
I <sub>IH</sub>	High-level input current (LVTTL inputs)	V <sub>IH</sub> = 2.0V		-15		15	μΑ
I <sub>IL</sub>	Low-level input current (LVTTL inputs)	$V_{IL} = 0.8V$		-15		15	μΑ
V <sub>IKL</sub>	Input Clamp Voltage (LVTTL inputs)	I <sub>IN</sub> = -18mA		-1.5			V
I <sub>OS</sub>	Differential short-circuit output current	See Figure 8		-43		43	mA
M-LVDS	Receiver						
$V_{IT+}$	Positive-going differential input voltage threshold	See FUNCTION TABLES	Type 1		20	50	mV
			Type 2		94	150	mV
V <sub>IT</sub> -	Negative-going differential input voltage threshold	See FUNCTION TABLES	Type 1	-50	20		mV
			Type 2	50	94		mV
V <sub>OH</sub>	High-level output voltage (LVTTL output)	I <sub>OH</sub> = −8mA	*	2.4	2.7		V
V <sub>OL</sub>	Low-level output voltage (LVTTL output)	I <sub>OL</sub> = 8mA			0.28	0.4	V
l <sub>oz</sub>	TRI-STATE output current	V <sub>O</sub> = 0V or 3.6V		-10		10	μΑ
I <sub>OSR</sub>	Short-circuit receiver output current (LVTTL output)	V <sub>O</sub> = 0V			-48	-90	mA
	Bus (Input and Output) Pins						
I <sub>A</sub>	Transceiver input/output current	V <sub>A</sub> = 3.8V, V <sub>B</sub> = 1.2V				32	μA
		$V_A = 0V \text{ or } 2.4V, V_B = 1.2V$	1	-20		+20	μA
		$V_A = -1.4V, V_B = 1.2V$		-32			μA
I <sub>B</sub>	Transceiver input/output current	$V_B = 3.8V, V_A = 1.2V$				32	μA
5	$V_{B} = 0V \text{ or } 2.4V, V_{A} = 1.2V$		,	-20		+20	μA
		$V_B = -1.4V, V_A = 1.2V$		-32		120	μA
I <sub>AB</sub>	Transceiver input/output differential current (I <sub>A</sub> - I <sub>B</sub> )	$V_A = V_B$ , $-1.4V \le V \le 3.8V$		-4		+4	μA
I <sub>A(OFF)</sub>	Transceiver input/output uniorental current (ig 1g)  Transceiver input/output power-off current	$V_{\Delta} = 3.8V, V_{B} = 1.2V,$				1-4	μΛ
, ,						32	μA
		$V_A = 0V \text{ or } 2.4V, V_B = 1.2V$ $DE = V_{CC}$ $0V \le V_{CC} \le 1.5V$	,	-20		+20	μΑ
		$V_A = -1.4V$ , $V_B = 1.2V$ , $DE = V_{CC}$ $0V \le V_{CC} \le 1.5V$		-32			μA
I <sub>B(OFF)</sub>	Transceiver input/output power-off current	$V_B = 3.8V, V_A = 1.2V,$ $DE = V_{CC}$ $0V \le V_{CC} \le 1.5V$				32	μΑ
		$V_B = 0V \text{ or } 2.4V, V_A = 1.2V,$ $DE = V_{CC}$ $0V \le V_{CC} \le 1.5V$		-20		+20	μΑ
		$V_B = -1.4V, V_A = 1.2V,$ $DE = V_{CC}$ $0V \le V_{CC} \le 1.5V$		-32			μA
I <sub>AB(OFF)</sub>	Transceiver input/output power-off differential current (I <sub>A(OFF)</sub> - I <sub>B(OFF)</sub> )	$V_A = V_B$ , $-1.4V \le V \le 3.8V$ , DE = $V_{CC}$ 0V $\le V_{CC} \le 1.5V$		-4		+4	μΑ
C <sub>A</sub>	Transceiver input/output capacitance	V <sub>CC</sub> = OPEN			9		pF
C <sub>B</sub>	Transceiver input/output capacitance				9		pF
C <sub>AB</sub>	Transceiver input/output differential capacitance				5.7		pF
C <sub>A/B</sub>	Transceiver input/output capacitance balance (C <sub>A</sub> /C <sub>B</sub> )				1.0		

(5) Not production tested. Specified by a statistical analysis on a sample basis at the time of characterization.

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#### **Electrical Characteristics (continued)**

Over recommended operating supply and temperature ranges unless otherwise specified. (1) (2) (3) (4)

	Parameter	Test Conditions	Min	Тур	Max	Units
SUPPLY (	CURRENT (V <sub>CC</sub> )					
I <sub>CCD</sub>	Driver Supply Current	$R_L = 50\Omega$ , $DE = V_{CC}$ , $\overline{RE} = V_{CC}$		20	29.5	mA
I <sub>CCZ</sub>	TRI-STATE Supply Current	DE = GND, RE = V <sub>CC</sub>		6	9.0	mA
I <sub>CCR</sub>	Receiver Supply Current	$DE = GND, \overline{RE} = GND$		14	18.5	mA

# **Switching Characteristics**

Over recommended operating supply and temperature ranges unless otherwise specified. (1) (2)

	Parameter	Test Conditions	Min	Тур	Max	Units
DRIVER AC S	SPECIFICATION					
t <sub>PLH</sub>	Differential Propagation Delay Low to High	$R_L = 50\Omega$ , $C_L = 5$ pF,	1.3	3.4	5.0	ns
t <sub>PHL</sub>	Differential Propagation Delay High to Low	C <sub>D</sub> = 0.5 pF Figure 9 and Figure 10	1.3	3.1	5.0	ns
t <sub>SKD1</sub> (t <sub>sk(p)</sub> )	Pulse Skew  t <sub>PLHD</sub> - t <sub>PHLD</sub>   (3) (4)	Tigure 3 and Figure 10		300	420	ps
t <sub>SKD3</sub>	Part-to-Part Skew (5) (5)				1.3	ns
t <sub>TLH</sub> (t <sub>r</sub> )	Rise Time (4)		1.0	1.8	3.0	ns
t <sub>THL</sub> (t <sub>f</sub> )	Fall Time (4)		1.0	1.8	3.0	ns
t <sub>PZH</sub>	Enable Time (Z to Active High)	$R_L = 50\Omega$ , $C_L = 5$ pF,			8	ns
t <sub>PZL</sub>	Enable Time (Z to Active Low)	C <sub>D</sub> = 0.5 pF See Figure 11 and Figure 12			8	ns
t <sub>PLZ</sub>	Disable Time (Active Low to Z)	Occ rigure in and rigure 12			8	ns
t <sub>PHZ</sub>	Disable Time (Active High to Z)				8	ns
t <sub>JIT</sub>	Random Jitter, RJ <sup>(4)</sup>	100 MHz Clock Pattern (6)		2.5	5.5	psrms
$f_{MAX}$	Maximum Data Rate		200			Mbps
RECEIVER A	C SPECIFICATION					
t <sub>PLH</sub>	Propagation Delay Low to High	C <sub>L</sub> = 15 pF	2.0	4.7	7.5	ns
t <sub>PHL</sub>	Propagation Delay High to Low	See Figure 13, Figure 14 and Figure 15	2.0	5.3	7.5	ns
$t_{SKD1} (t_{sk(p)})$	Pulse Skew  t <sub>PLHD</sub> - t <sub>PHLD</sub>   (3) (4)			0.6	1.7	ns
t <sub>SKD3</sub>	Part-to-Part Skew (5) (4)				1.3	ns
t <sub>TLH</sub> (t <sub>r</sub> )	Rise Time (4)		0.5	1.2	2.5	ns
t <sub>THL</sub> (t <sub>f</sub> )	Fall Time (4)		0.5	1.2	2.5	ns
t <sub>PZH</sub>	Enable Time (Z to Active High)	$R_L = 500\Omega$ , $C_L = 15 pF$			10	ns
t <sub>PZL</sub>	Enable Time (Z to Active Low)	See Figure 16 and Figure 17			10	ns
t <sub>PLZ</sub>	Disable Time (Active Low to Z)				10	ns
t <sub>PHZ</sub>	Disable Time (Active High to Z)				10	ns
f <sub>MAX</sub>	Maximum Data Rate		200			Mbps

<sup>(1)</sup> All typicals are given for  $V_{CC} = 3.3V$  and  $T_A = 25$ °C.

Product Folder Links: DS91C176 DS91D176

Stimulus and fixture Jitter has been subtracted.

<sup>(2)</sup> C<sub>L</sub> includes fixture capacitance and C<sub>D</sub> includes probe capacitance.

t<sub>SKD1</sub>, |t<sub>PLHD</sub> - t<sub>PHLD</sub>|, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

<sup>(4)</sup> Not production tested. Specified by a statistical analysis on a sample basis at the time of characterization.

t<sub>SKD3</sub>, Part-to-Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V<sub>CC</sub> and within 5°C of each other within the operating temperature range.



## **Test Circuits and Waveforms**

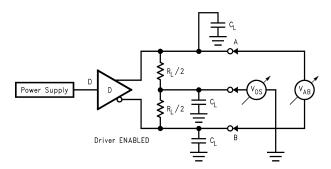


Figure 4. Differential Driver Test Circuit

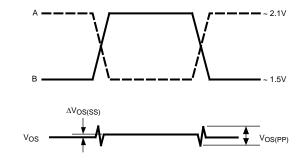


Figure 5. Differential Driver Waveforms

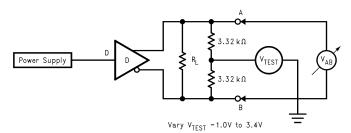


Figure 6. Differential Driver Full Load Test Circuit

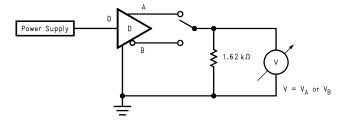


Figure 7. Differential Driver DC Open Test Circuit



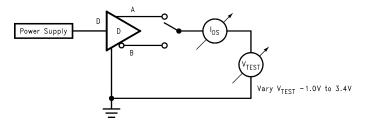


Figure 8. Differential Driver Short-Circuit Test Circuit

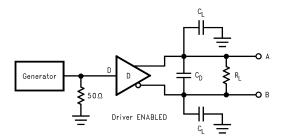


Figure 9. Driver Propagation Delay and Transition Time Test Circuit

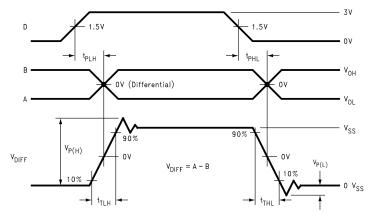


Figure 10. Driver Propagation Delays and Transition Time Waveforms

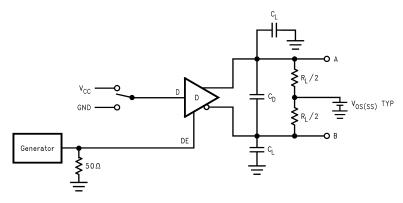


Figure 11. Driver TRI-STATE Delay Test Circuit



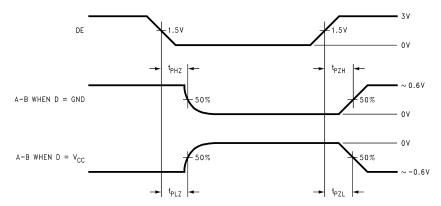


Figure 12. Driver TRI-STATE Delay Waveforms

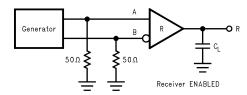


Figure 13. Receiver Propagation Delay and Transition Time Test Circuit

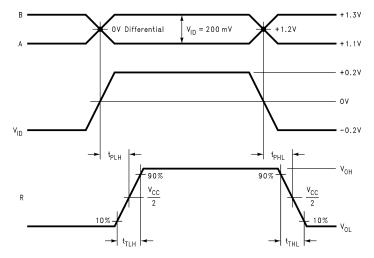


Figure 14. Type 1 Receiver Propagation Delay and Transition Time Waveforms



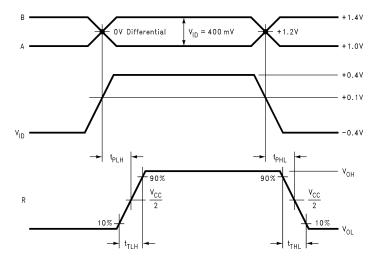


Figure 15. Type 2 Receiver Propagation Delay and Transition Time Waveforms

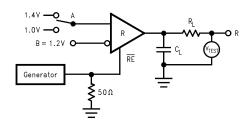


Figure 16. Receiver TRI-STATE Delay Test Circuit

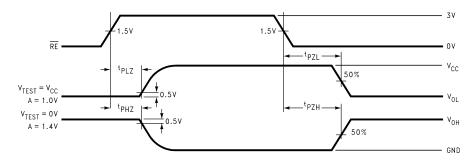


Figure 17. Receiver TRI-STATE Delay Waveforms

### **FUNCTION TABLES**

Table 1. DS91D176/DS91C176 Transmitting(1)

Inputs		Out	puts	
RE	DE	D	В	Α
Х	2.0V	2.0V	L	Н
Х	2.0V	0.8V	Н	L
X	0.8V	X	Z	Z

X — Don't care conditionZ — High impedance state



## Table 2. DS91D176 Receiving<sup>(1)</sup>

	Inputs	Output	
RE	DE	A – B	R
0.8V	0.8V	≥ +0.05V	Н
0.8V	0.8V	≤ -0.05V	L
0.8V	0.8V	0V	X
2.0V	0.8V	X	Z

X — Don't care condition Z — High impedance state

# Table 3. DS91C176 Receiving<sup>(1)</sup>

	Inputs		
RE	DE	A – B	R
0.8V	0.8V	≥ +0.15V	Н
0.8V	0.8V	≤ +0.05V	L
0.8V	0.8V	0V	L
2.0V	0.8V	X	Z

X — Don't care condition Z — High impedance state

## Table 4. DS91D176 Receiver Input Threshold Test Voltages (1)

Applied	Voltages	Resulting Differential Input Voltage	Resulting Common-Mode Input Voltage	Receiver Output
V <sub>IA</sub>	V <sub>IB</sub>	$V_{ID}$	V <sub>IC</sub>	R
2.400V	0.000V	2.400V	1.200V	Н
0.000V	2.400V	-2.400V	1.200V	L
3.800V	3.750V	0.050V	3.775V	Н
3.750V	3.800V	-0.050V	3.775V	L
-1.400V	-1.350V	-0.050V	-1.375V	Н
-1.350V	-1.400V	0.050V	-1.375V	L

(1) H — High Level L — Low Level

Output state assumes that the receiver is enabled ( $\overline{RE} = L$ )

# Table 5. DS91C176 Receiver Input Threshold Test Voltages<sup>(1)</sup>

Applied	l Voltages	Resulting Differential Input Voltage	Resulting Common-Mode Input Voltage	Receiver Output
V <sub>IA</sub>	V <sub>IB</sub>	V <sub>ID</sub>	V <sub>IC</sub>	R
2.400V	0.000V	2.400V	1.200V	Н
0.000V	2.400V	-2.400V	1.200V	L
3.800V	3.650V	0.150V	3.725V	Н
3.800V	3.750V	0.050V	3.775V	L
-1.250V	-1.400V	0.150V	-1.325V	Н
-1.350V	-1.400V	0.050V	-1.375V	L

(1) H — High Level L — Low Level

Output state assumes that the receiver is enabled ( $\overline{RE} = L$ )

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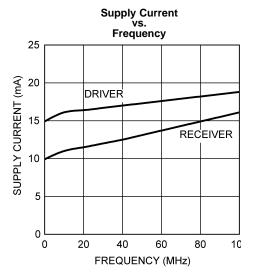


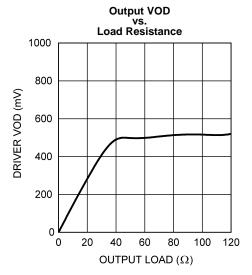
### **PIN DESCRIPTONS**

Pin No.	Name	Description
1	R	Receiver output pin
2	RE	Receiver enable pin: When $\overline{RE}$ is high, the receiver is disabled. When $\overline{RE}$ is low or open, the receiver is enabled.
3	DE	Driver enable pin: When DE is low, the driver is disabled. When DE is high, the driver is enabled.
4	D	Driver input pin
5	GND	Ground pin
6	Α	Non-inverting driver output pin/Non-inverting receiver input pin
7	В	Inverting driver output pin/Inverting receiver input pin
8	$V_{CC}$	Power supply pin, +3.3V ± 0.3V



# Typical Performance Characteristics – DS91D176/DS91C176





Supply Current measured using a clock pattern with driver terminated  $V_{CC}=3.3V$ ,  $T_A=+25^{\circ}C$  to 50ohms .  $V_{CC}=3.3V$ ,  $T_A=+25^{\circ}C$ . Figure 18.

Figure 19.





## **REVISION HISTORY**

CI	hanges from Revision K (April 2013) to Revision L	Pa	ge
•	Changed layout of National Data Sheet to TI format		12



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#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
DS91C176TMA/NOPB	ACTIVE	SOIC	D	8	95	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91C 176MA	Samples
DS91C176TMAX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91C 176MA	Samples
DS91D176TMA/NOPB	ACTIVE	SOIC	D	8	95	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91D 176MA	Samples
DS91D176TMAX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91D 176MA	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE OPTION ADDENDUM

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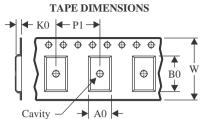
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# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS91C176TMAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
DS91D176TMAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS91C176TMAX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
DS91D176TMAX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0

# **PACKAGE MATERIALS INFORMATION**

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### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
DS91C176TMA/NOPB	D	SOIC	8	95	495	8	4064	3.05
DS91D176TMA/NOPB	D	SOIC	8	95	495	8	4064	3.05



SMALL OUTLINE INTEGRATED CIRCUIT



### NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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